

## AMENDMENTS TO THE CLAIMS

1. (Currently Amended) An apparatus comprising:  
a plurality of circuit substrates on a substrate and the plurality of circuit substrates are in a non-planar orientation relative to one another stacked one on the other, each circuit substrate consisting of a single crystal semiconductor layer having a smallest dimension reduced prior to stacking;  
circuit devices formed in the single crystal layer of each of the plurality of circuit substrates; and  
a plurality of interconnects disposed between the plurality of circuit substrates.
2. (Canceled)
3. (Canceled)
4. (Previously Presented) The apparatus of claim 1, wherein the circuit devices form integrated circuits that interact with other electrical devices off the single crystal layer on which the integrated circuits are formed.
5. (Previously Presented) The apparatus of claim 1, wherein the smallest dimension of each circuit substrate comprises a thickness less than 100 microns.
6. (Previously Presented) The apparatus of claim 1, further comprising a dielectric material disposed between the adjacent ones of the plurality of circuit substrates.